

SILICON PHOTODIODE VTP8740STRH

FEATURES

- Surface mount package
- Low capacitance
- Fast response
- High shunt impedance
- Tape & reel supplied

PRODUCT DESCRIPTION

This planar silicon photodiode features a lensed, water clear epoxy package suitable for surface mount assembly in a "side mounted" orientation.

These photodiodes exhibit performance charac teristics which make them suitable for a wide range of near-IR sensing applications. Devices are shipped taped & reeled on a 24 mm embossed carrier.

ELECTRO-OPTICAL CHARACTERISTICS @ 25° C

PARAMETER	SYMB(OL MIN	TYP	MAX	UNITS
SHORT CIRCUIT CURRENT @ 100 fc, 2850 f	\ ISC	75	90		μА
DARK CURRENT @ V _R = 10 V	ΙD			20	nA
SHUNT RESISTANCE @ H = 0, V = 10 mV	R _{SH}		0.25		GΩ
JUNCTION CAPACITANCE @ V _R = 3 V	СJ			50	pF
OPEN CIRCUIT VOLTAGE @ 100 fc, 2850 K	Voc	325			mV
ANGULAR RESPONSE (50% RESPONSE POINT)	θ1/2		±42		Degrees

.20 [5.1] -

[1.45]

14 [3.6] .057

PACKAGE DIMENSIONS inch (mm)

.04 [1.0]

35°

 $.394 \pm .008 [10.00 \pm 0.20] -$

- .276 [7.00]

Ø.165 [4.20]

R.087 [2.20]

.197

[5.00]

.063 NOM

.020 ± .008

 $[0.50 \pm 0.20]$

(2X)

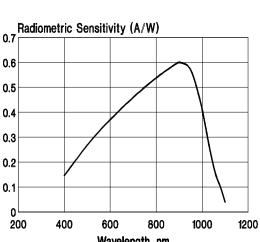
MATTE FINISH

.04 ± .004

 $[1.0 \pm 0.1]$

(2X)

RoHS Compliant



TYPICAL SPECTRAL RESPUNSE

CATHODE ID

.04 ± .008

 $[1.0 \pm 0.2]$

(2X) .028 ± .004

[0.70 ±0.10]

(2X)

.04 ±.008

 $[1.0 \pm 0.2]$

.030 [0.76]

5°(8X)

0-3°(3X)

 $.031 \pm .008$ [0.80 ± 0.20]

LEAD BEND 1-8° (2X)

Tolerances unless

otherwise noted: ±.010 [±0.25]

GENERAL CHARACTERISTICS

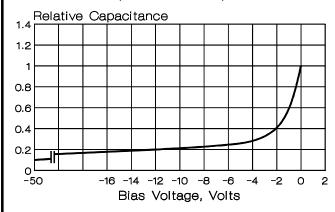
PARAMETER	SYMBOL	TYPICAL RATING	UNITS
PEAK SPECTRAL RESPONSE @ 25°C	λ_{P}	925	nm
RADIOMETRIC SENSITIVITY @ PEAK, 25°C	S _{RPK}	0.6	A / W
NOISE EQUIVALENT POWER	NEP	2.0 x 10 ⁻¹³	W/ √Hz
SPECIFIC DETECTIVITY	D*	1.2 x 10 ¹²	cm √Hz /W
TEMPERATURE COEFFICIENT SHORT CIRCUIT CURRENT @ 2850 K SOURCE OPEN CIRCUIT VOLTAGE @ 2850 K SOURCE DARK CURRENT	TC I _{SC} TC V _{OC} TC I _D	+0.22 - 2.0 +15.0	%/°C mV/ C %/°C

ABSOLUTE MAXIMUM RATINGS

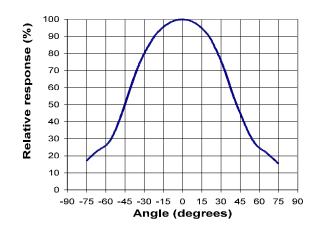
PARAMETER	SYMBOL	RATING	UNITS
TEMPERATURE RANGE OPERATING AND STORAGE	Тамв	– 40 to +85	°C
LEAD SOLDER TEMPERATURE (1.6 mm FROM CASE, 5 SECONDS MAX.)	TLS	260°	°C
BREAKDOWN VOLTAGE @ 25°C	V_{BR}	33	Volts
POWER DISSIPATION	P_{D}	150	mW

TYPICAL CHARACTERISTIC CURVES

RELATIVE JUNCTION CAPACITANCE vs BIAS VOLTAGE (REFERRED TO ZERO BIAS)



ANGULAR RESPONSE



Specifications subject to change without prior notice. Information supplied by Excelitas Technologies is believed to be reliable, however, no responsibility is assumed for possible inaccuracies or omissions. The user should determine the suitability of this product in his own application. No patent rights are granted to any devices or circuits described herein.